

Data Sheet	January 2002	

30A, 600V Ultrafast Diode

The RURP3060 is an ultrafast diode ($t_{rr} < 55$ ns) with soft recovery characteristics. It has a low forward voltage drop and is of planar, silicon nitride passivated, ion-implanted, epitaxial construction.

This device is intended for use as an energy steering/ clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristics minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistor.

Formerly developmental type TA09903.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RURP3060	TO-220AC	RURP3060

NOTE: When ordering, use the entire part number.

Symbol



Features

•	Ultrafast with Soft Recovery< 55ns
•	Operating Temperature
•	Reverse Voltage

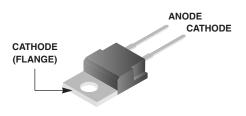
- Avalanche Energy Rated
- Planar Construction

Applications

- · Switching Power Supply
- · Power Switching Circuits
- · General Purpose

Packaging

JEDEC TO-220AC



Absolute Maximum Ratings T_C = 25°C, Unless Otherwise Specified

	RURP3060	UNITS
Peak Repetitive Reverse Voltage	600	V
Working Peak Reverse Voltage	600	V
DC Blocking Voltage	600	V
Average Rectified Forward Current (T _C = 130°C)	30	Α
Repetitive Peak Surge Current	70	А
Nonrepetitive Peak Surge Current	325	Α
Maximum Power Dissipation	125	W
Avalanche Energy (See Figures 7 and 8)	20	mJ
Operating and Storage Temperature	-55 to 175	°C

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	ТҮР	MAX	UNITS
V _F	I _F = 30A	-	-	1.5	V
	$I_F = 30A, T_C = 150^{\circ}C$	-	-	1.3	V
I _R	V _R = 600V	-	-	250	μА
	$V_R = 600V, T_C = 150^{\circ}C$	-	-	1	mA
t _{rr}	I _F = 1A, dI _F /dt = 100A/μs	-	-	55	ns
	$I_F = 30A$, $dI_F/dt = 100A/\mu s$	-	-	60	ns
ta	I _F = 30A, dI _F /dt = 100A/μs	-	30	-	ns
t _b	I _F = 30A, dI _F /dt = 100A/μs	-	20	-	ns
$R_{ heta JC}$		-	-	1.2	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

I_R = Instantaneous reverse current.

 t_{rr} = Reverse recovery time at dI_F/dt = 100A/ μ s (See Figure 6), summation of t_a + t_b .

 t_a = Time to reach peak reverse current at dI_F/dt = 100A/ μ s (See Figure 6).

 t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

Typical Performance Curves

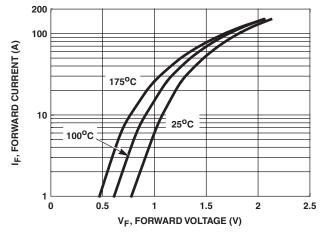


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

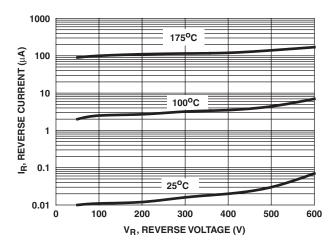


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

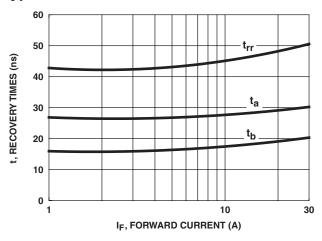


FIGURE 3. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

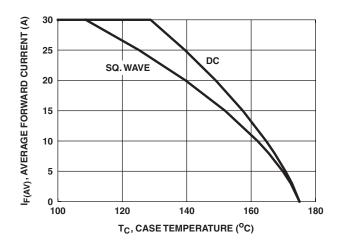


FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

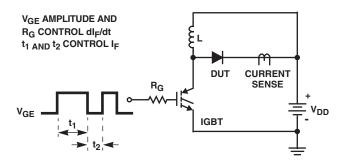
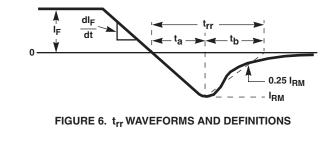


FIGURE 5. t_{rr} TEST CIRCUIT



I = 1A L = 40mH $R < 0.1\Omega$ $E_{AVL} = 1/2LI^2 \left[V_{R(AVL)} / (V_{R(AVL)} - V_{DD}) \right]$ $Q_1 = IGBT \left(BV_{CES} > DUT \, V_{R(AVL)} \right)$ CURRENT + o $SENSE V_{DD}$ V_{DD} DUT - o

FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

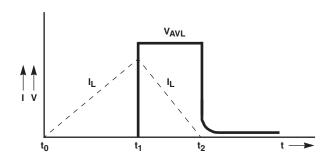


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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